BLF6G27-100; BLF6G27LS-100

WiMAX power LDMOS transistor Rev. 02 — 8 July 2010

Product data sheet

Product profile 1.

1.1 General description

100 W LDMOS power transistor for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. **Typical performance**

Typical RF performance at $T_{case} = 25$ °C in a class-AB production test circuit.

| Mode of operation | f | V_{DS} | P _{L(AV)} | Gp | ηD | ACPR _{885k} | ACPR _{1980k} | ACPR _{5M} | ACPR _{10M} |
|----------------------|--------------|----------|--------------------|------|-----|----------------------|-----------------------|--------------------|---------------------|
| | (MHz) | (V) | (W) | (dB) | (%) | (dBc) | (dBc) | (dBc) | (dBc) |
| BLF6G27-100 | | | | | | | | | |
| 1-carrier W-CDMA [1] | 2500 to 2700 | 28 | 14 | 16.5 | 23 | - | - | -40 | -59 |
| 1-carrier N-CDMA [2] | 2500 to 2700 | 28 | 14 | 17 | 23 | -50 <u>[3]</u> | -65 <u>[3]</u> | - | - |
| BLF6G27LS-100 | | | | | | | | | |
| 1-carrier W-CDMA [1] | 2500 to 2700 | 28 | 14 | 17 | 23 | - | - | -41 | -60 |
| 1-carrier N-CDMA [2] | 2500 to 2700 | 28 | 14 | 17 | 23 | -50 <u>[3]</u> | -65 <u>[3]</u> | - | - |

^[1] Signal is a one carrier, TM1 W-CDMA signal with 64 DPCH and 100 % clipping. PAR is 9.65 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Typical 1-carrier W-CDMA performance (single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability on the CCDF; channel bandwidth is 3.84 MHz) at a frequency of 2500 MHz, 2600 MHz and 2700 MHz, a supply voltage of 28 V and an I_{Dq} of 900 mA:
 - Average output power = 14 W
 - ◆ Power gain = 17 dB
 - Drain efficiency = 23 %
 - ◆ ACPR_{5M} = -41 dBc
- Typical 1-carrier N-CDMA performance (single carrier IS-95 with pilot, paging, sync and 6 traffic channels [Walsh codes 8 to 13]. PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz) at a frequency of 2500 MHz, 2600 MHz and 2700 MHz, a supply voltage of 28 V and an I_{Dq} of 900 mA:
 - Average output power = 14 W
 - Power gain = 17 dB
 - Drain efficiency = 23 %
 - ◆ ACPR_{885k} = -50 dBc (within 30 kHz bandwidth)



Single carrier IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13). PAR = 9.7 dB at 0.01 % probability on the CCDF. Channel bandwidth is 1.2288 MHz.

Measured within 30 kHz bandwidth.

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (2500 MHz to 2700 MHz)
- Internally matched for ease of use

1.3 Applications

 RF power amplifiers for base stations and multicarrier applications in the 2500 MHz to 2700 MHz frequency range

2. Pinning information

Table 2. Pinning

| Table 2. | Pinning | | |
|----------|-------------------|---|--------------------|
| Pin | Description | Simplified outline | Graphic symbol |
| BLF6G27 | ′-100 (SOT502A) | | |
| 1 | drain | | |
| 2 | gate | $\begin{array}{c c} & & \\ & & \\ & & \\ \end{array}$ | ئے |
| 3 | source | [1] | 2 |
| | | | · 3 sym112 |
| | | | Syminz |
| BLF6G27 | 'LS-100 (SOT502B) | | |
| 1 | drain | | |
| 2 | gate | 3 | 1 |
| 3 | source | [1] | 2 |
| | | | 3 |
| | | | sym112 |

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|---------------|---------|---|---------|--|--|--|
| | Name | Description | Version | | | |
| BLF6G27-100 | - | flanged LDMOST ceramic package; 2 mounting holes; 2 leads | SOT502A | | | |
| BLF6G27LS-100 | - | earless flanged LDMOST ceramic package; 2 leads | SOT502B | | | |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Min | Max | Unit |
|------------------|----------------------|------|------|------|
| V_{DS} | drain-source voltage | - | 65 | V |
| V_{GS} | gate-source voltage | -0.5 | +13 | V |
| I_D | drain current | - | 29 | А |
| T _{stg} | storage temperature | -65 | +150 | °C |
| T _i | junction temperature | - | 200 | °C |

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Туре | Тур | Unit |
|-------------------------|-------------------------|-----------------------------------|---------------|------|------|
| $R_{\text{th(j-case)}}$ | thermal resistance from | T_{case} = 80 °C; P_L = 100 W | BLF6G27-100 | 0.68 | K/W |
| | junction to case | | BLF6G27LS-100 | 0.5 | K/W |

6. Characteristics

Table 6. Characteristics

 $T_i = 25$ °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|----------------------------------|--|------|------|------|------|
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $V_{GS} = 0 \text{ V}; I_D = 0.5 \text{ mA}$ | 65 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $V_{DS} = 10 \text{ V}; I_D = 150 \text{ mA}$ | 1.4 | 2 | 2.4 | V |
| I_{DSS} | drain leakage current | $V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$ | - | - | 5 | μΑ |
| I _{DSX} | drain cut-off current | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$ | 22.3 | 27 | - | Α |
| I_{GSS} | gate leakage current | $V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$ | - | - | 450 | nA |
| 9 _{fs} | forward transconductance | $V_{DS} = 10 \text{ V}; I_D = 5.25 \text{ A}$ | - | 10.5 | - | S |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.25 \text{ A}$ | - | 0.1 | 0.16 | Ω |
| C_{rs} | feedback capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V};$ f = 1 MHz | - | 2.4 | - | pF |

7. Application information

Table 7. Application information

Mode of operation: 1-carrier W-CDMA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability on the CCDF; carrier channel bandwidth is 3.84 MHz; f_1 = 2500 MHz; f_2 = 2600 MHz, f_3 = 2700 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 900 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB production circuit.

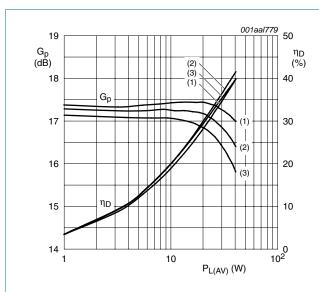
| | | • | | | | | |
|---------------------|---------------------------------------|--------------------|-----|------|------|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| G_p | power gain | $P_{L(AV)} = 14 W$ | | | | | |
| | | BLF6G27-100 | | 14.8 | 16.5 | - | dB |
| | | BLF6G27LS-100 | | 15 | 17 | - | dB |
| RLin | input return loss | $P_{L(AV)} = 14 W$ | | - | -10 | -6 | dB |
| η_{D} | drain efficiency | $P_{L(AV)} = 14 W$ | | 20 | 23 | - | % |
| ACPR _{5M} | adjacent channel power ratio (5 MHz) | $P_{L(AV)} = 14 W$ | [1] | | | | |
| | | BLF6G27-100 | | - | -40 | -36 | dBc |
| | | BLF6G27LS-100 | | - | -41 | -37 | dBc |
| ACPR _{10M} | adjacent channel power ratio (10 MHz) | $P_{L(AV)} = 14 W$ | [1] | | | | |
| | | BLF6G27-100 | | - | -59 | -56 | dBc |
| | | BLF6G27LS-100 | | - | -60 | -57 | dBc |
| | | | | | | | |

^[1] ACPR measured in 3.84 MHz channel bandwidth at ± 5 MHz and ± 10 MHz.

7.1 Ruggedness in class-AB operation

The BLF6G27-100 and BLF6G27LS-100 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; $I_{Dq} = 900 \text{ mA}$; $P_L = 100 \text{ W}$ (CW); f = 2500 MHz.

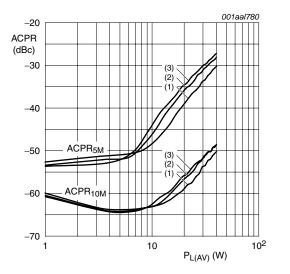
7.2 Single carrier W-CDMA performance



 $V_{DS}=28$ V; $I_{Dq}=900$ mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 1. Power gain and drain efficiency as a function of average output power; typical values

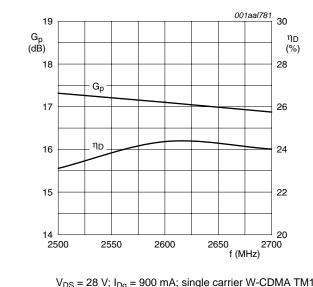


 V_{DS} = 28 V; I_{Dq} = 900 mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

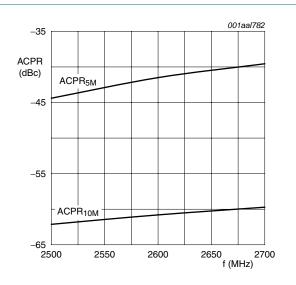
Fig 2. ACPR at 5 MHz and at 10 MHz as a function of average output power; typical values

7.3 Single carrier W-CDMA broadband performance at 14 W average power



 V_{DS} = 28 V; I_{Dq} = 900 mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

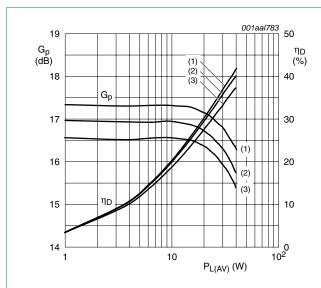
Power gain and drain efficiency as a function Fig 3. of frequency; typical values



 V_{DS} = 28 V; I_{Dq} = 900 mA; single carrier W-CDMA TM1 with 64 DPCH and 100 % clipping; PAR = 9.65 dB at 0.01 % probability; channel bandwidth = 3.84 MHz.

Fig 4. ACPR at 5 MHz and at 10 MHz as a function of frequency; typical values

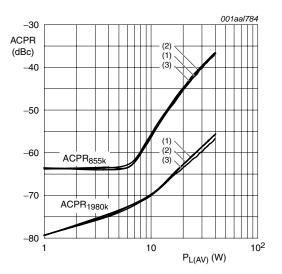
7.4 IS-95 performance



 $V_{DS}=28\ V;\ I_{Dq}=900\ mA;\ IS-95\ with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.$

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

Fig 5. Power gain and drain efficiency as a function of average output power; typical values

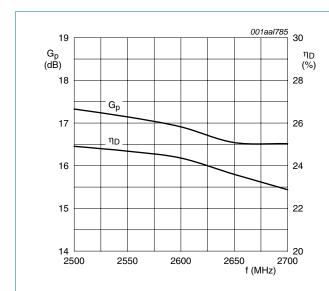


 $V_{DS}=28\ V;\ I_{Dq}=900\ mA;\ IS-95$ with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.

- (1) f = 2500 MHz
- (2) f = 2600 MHz
- (3) f = 2700 MHz

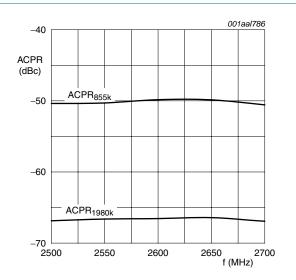
Fig 6. ACPR at 885 kHz and at 1980 kHz as a function of average output power; typical values

7.5 IS-95 broadband performance at 14 W average power



 $V_{DS}=28\ V;\ I_{Dq}=900\ mA;\ IS-95$ with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.

Fig 7. Power gain and drain efficiency as a function of frequency; typical values



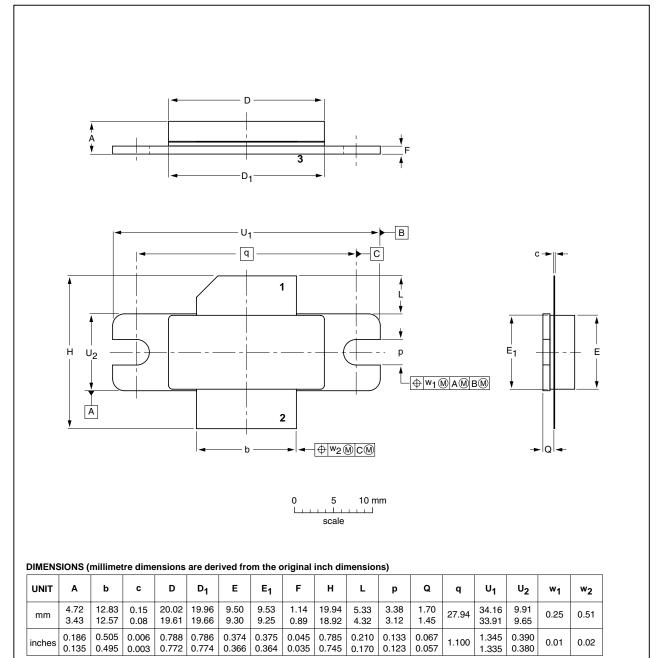
 V_{DS} = 28 V; I_{Dq} = 900 mA; IS-95 with pilot, paging, sync and 6 traffic channels (Walsh codes 8 to 13); PAR = 9.7 dB at 0.01 % probability on the CCDF; channel bandwidth = 1.2288 MHz.

Fig 8. ACPR at 885 kHz and at 1980 kHz as a function of frequency; typical values

8. Package outline



SOT502A



| OUTLINE | | REFER | RENCES | EUROPEAN | ISSUE DATE | |
|---------|-----|-------|--------|------------|---------------------------------|--|
| VERSION | IEC | JEDEC | JEITA | PROJECTION | | |
| SOT502A | | | | | 99-12-28 03-01-10 | |

Fig 9. Package outline SOT502A

BLF6G27-100_BLF6G27LS-100

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Earless flanged LDMOST ceramic package; 2 leads

SOT502B

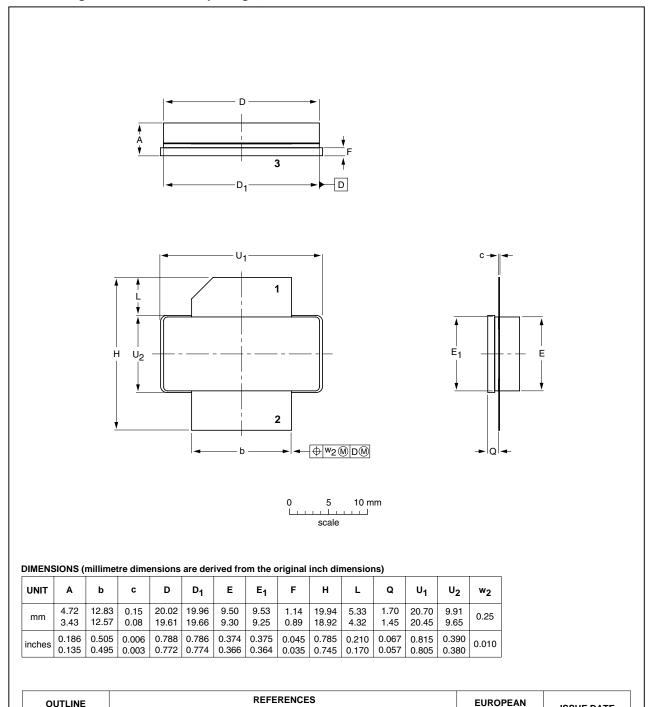


Fig 10. Package outline SOT502B

IEC

JEDEC

VERSION

SOT502B

JEITA

ISSUE DATE

03-01-10

PROJECTION

9. Abbreviations

Table 8. Abbreviations

| Acronym | Description |
|---------|---|
| CCDF | Complementary Cumulative Distribution Function |
| CW | Continuous Wave |
| DPCH | Dedicated Physical CHannel |
| ESD | ElectroStatic Discharge |
| FCH | Frame Control Header |
| FFT | Fast Fourier Transform |
| IBW | Instantaneous BandWidth |
| IS-95 | Interim Standard 95 |
| LDMOS | Laterally Diffused Metal-Oxide Semiconductor |
| N-CDMA | Narrowband Code Division Multiple Access |
| PAR | Peak-to-Average power Ratio |
| PUSC | Partial Usage of SubChannels |
| RF | Radio Frequency |
| TM1 | Test Model 1 |
| VSWR | Voltage Standing-Wave Ratio |
| W-CDMA | Wideband Code Division Multiple Access |
| WCS | Wireless Communications Service |
| WiMAX | Worldwide interoperability for Microwave Access |
| | |

10. Revision history

Table 9. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------------------|--------------------------------|---------------------------------|------------------|---------------------------------|
| BLF6G27-100_BLF6G27LS-100 v.2 | 20100708 | Product data sheet | - | BLF6G27-100_ BLF6G27LS-100_1 |
| Modifications: | Data sheet | status change to Product | data sheet. | |
| | • Table 1 on BLF6G27L | page 1: A distinction has S-100 | been made betwee | n BLF6G27-100 and |
| | • Table 7 on BLF6G27L | page 4: A distinction has S-100 | been made betwee | n BLF6G27-100 and |
| BLF6G27-100_BLF6G27LS-100_1 | 20100503 | Preliminary data sheet | - | - |

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|--------------------------------|-------------------|---|
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BLF6G27-100; BLF6G27LS-100

WiMAX power LDMOS transistor

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